

特性及特性种类 Characteristic and Characteristic varieties		单晶硅片参数 Monocrystalline silicon chip parameters
几何及外观特性 DIMENSIONAL AND SURFACE CHARACTERISTICS	规格Specification	182.2*182.2单晶
	边长Length of side	182.2±0.25mm
	对角线Diagonal	247±0.25mm
	四边垂直度Squareness	90° ±0.15°
	硅片中心厚度Center thickness	130±10 μm, 均值≥130
	总厚度差异Total Thickness Variation	≤25μm
	翘曲度Warp	≤40μm
	线痕深度Saw mark	≤13μm
	弧长Arc length	7.72±0.45mm
	缺口Indent	不可有 Not allowed
	裂纹Crack	不可有 Not allowed
	线纹方向Line marks	方向一致 In the same direction
	崩边Edge chip	≤长0.5(length)mm*宽(width)0.3mm, 每片不超过2个 (not more than 2 per wafer)
	表面质量Surface condition	硅片表面无明显线痕, 手感不明显; 无凹坑; 无硅胶残留; 表面无沾污和异常斑点、无色差。 No obviou saw mark ,no naked obvious tactility;no pinglue residues;surface cleaned ,no abnormal spo or stai.
电性能参数 ELECTRICAL CHARACTERISTICS	电阻率Resistivity	0.4-1.6 Ω · cm
	少子寿命Life Time	≥800μs (BCT-400)
常规特性 GENERAL CHARACTERISTICS	生长方法Growth method	CZ直拉法
	掺杂剂Dopant	磷 P
	导电类型Conduction Type	N型
	氧含量Oxygen concentration	≤6.0*10 ¹⁷ atoms/cm ³
	碳含量Carbon concentration	≤0.5*10 ¹⁷ atoms/cm ³
包装与标识Package and Label	包装Package	175片/包, 2800片/盒, 78400片/托; 175pcs/unit, 2800pcs/box, 78400pcs/pallet
	标识Label	批号, 数量, 厚度, 电阻等; Lngot Lot No, Quantity, Thickness, Resistivity etc
备注Remarks		
编制Draft: 高艳洁 2025-2-25 审核Review: 徐书华 2025-2-25 批准Approval: 徐书华 2025-2-25		